MAC15M, MAC15N

Triacs

Silicon Bidirectional Thyristors

Designed for high performance full-wave AC control applications where high noise immunity and high commutating di/dt are required.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 15 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Modes
- High Immunity to dv/dt – 250 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO–220 Package
- High Commutating di/dt – 9.0 A/ms minimum at 125°C
- Operational in Three Quadrants, Q1, Q2, and Q3
- These Devices are Pb–Free and are RoHS Compliant*

ON Semiconductor®

TRIACS
15 AMPERES RMS
600 thru 800 VOLTS

MT2 ○——▷◁——○ MT1
          └○ G

**MARKING
DIAGRAM**

MAC15xG
AYWW

**TO–220
CASE 221A
STYLE 4**

1
2
3

x   = M or N
A   = Assembly Location
Y   = Year
WW = Work Week
G   = Pb–Free Package

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (–40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MAC15M MAC15N	V_{DRM}, V_{RRM}	600 800	V
On–State RMS Current (Full Cycle Sine Wave, 60 Hz, T_C = 80°C)	$I_{T(RMS)}$	15	A
Peak Non-repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T_J = 125°C)	I_{TSM}	150	A
Circuit Fusing Consideration (t = 8.3 ms)	I^2t	93	A^2s
Peak Gate Power (Pulse Width ≤ 1.0 μs, T_C = 80°C)	P_{GM}	20	W
Average Gate Power (t = 8.3 ms, T_C = 80°C)	$P_{G(AV)}$	0.5	W
Operating Junction Temperature Range	T_J	–40 to +125	°C
Storage Temperature Range	T_{stg}	–40 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
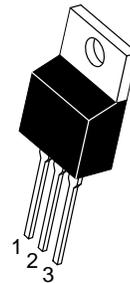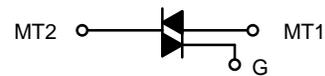
1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
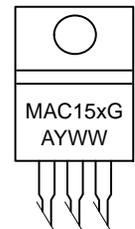
PIN ASSIGNMENT

1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
MAC15MG	TO–220 (Pb–Free)	50 Units / Rail
MAC15NG	TO–220 (Pb–Free)	50 Units / Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAC15M, MAC15N

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction−to−Case Junction−to−Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted; Electricals apply in both directions)

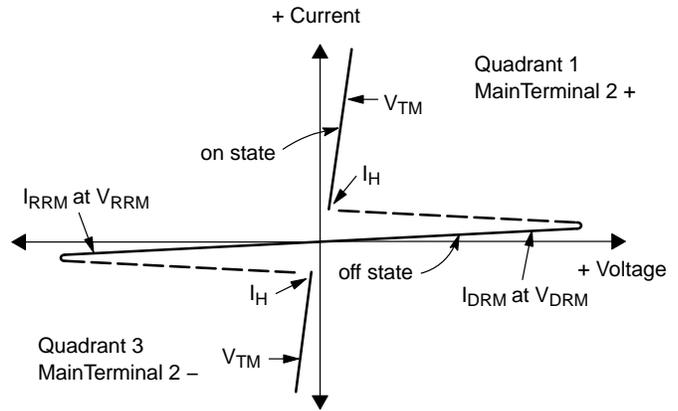| Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Blocking Current (V_D = Rated V_{DRM}, V_{RRM}; Gate Open) T_J = 25°C T_J = 125°C		I_{DRM}, I_{RRM}	− −	− −	0.01 2.0	mA
ON CHARACTERISTICS						
Peak On-State Voltage (Note 2) (I_{TM} = ±21 A Peak)		V_{TM}	−	1.2	1.6	V

Gate Trigger Current (Continuous DC) (V_D = 12 V, R_L = 100 Ω)
  MT2(+), G(+)
  MT2(+), G(−)
  MT2(−), G(−)
		I_{GT}	5.0
			5.0
			5.0
				13
				16
				18
					35
					35
					35
						mA

Hold Current (V_D = 12 Vdc, Gate Open, Initiating Current = ±150 mA)		I_H	−	20	40	mA

Latching Current (V_D = 24 V, I_G = 35 mA)
  MT2(+), G(+)
  MT2(+), G(−)
  MT2(−), G(−)
		I_L	−
			−
			−
				33
				36
				33
					50
					80
					50
						mA

Gate Trigger Voltage (V_D = 12 V, R_L = 100 Ω)
  MT2(+), G(+)
  MT2(+), G(−)
  MT2(−), G(−)
		V_{GT}	0.5
			0.5
			0.5
				0.75
				0.72
				0.82
					1.5
					1.5
					1.5
						V

DYNAMIC CHARACTERISTICS						
Rate of Change of Commutating Current; See Figure 10. (V_D = 400 V, I_{TM} = 6.0 A, Commutating dv/dt = 24 V/μs, C_L = 10 μF Gate Open, T_J = 125°C, f = 250 Hz, No Snubber) L_L = 40 mH		$(di/dt)_c$	9.0	−	−	A/ms
Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM}, Exponential Waveform, Gate Open, T_J = 125°C)		dv/dt	250	−	−	V/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
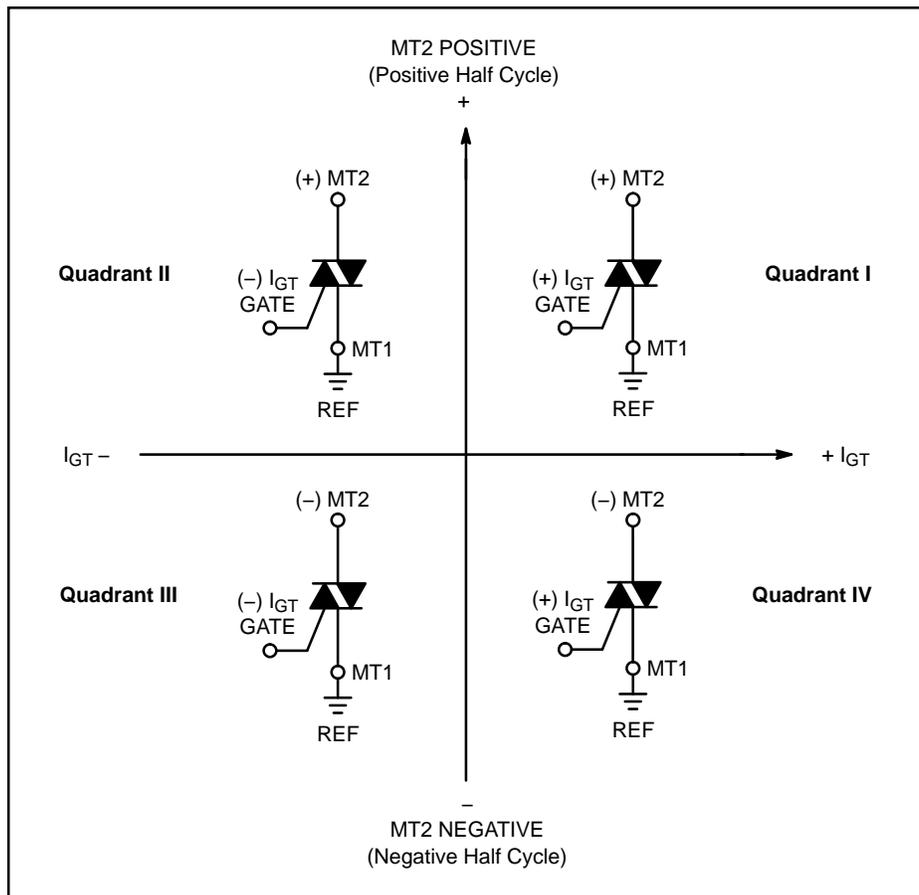2. Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

MAC15M, MAC15N

Voltage Current Characteristic of Triacs
(Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current

Quadrant Definitions for a Triac

MT2 POSITIVE
(Positive Half Cycle)
+

(+) MT2

Quadrant II   (−) I_{GT} GATE   MT1   REF

(+) MT2

(+) I_{GT} GATE   MT1   REF   **Quadrant I**

I_{GT} −   + I_{GT}

(−) MT2

Quadrant III   (−) I_{GT} GATE   MT1   REF

(−) MT2

(+) I_{GT} GATE   MT1   REF   **Quadrant IV**

−
MT2 NEGATIVE
(Negative Half Cycle)

All polarities are referenced to MT1.
With in–phase signals (using standard AC lines) quadrants I and III are used.
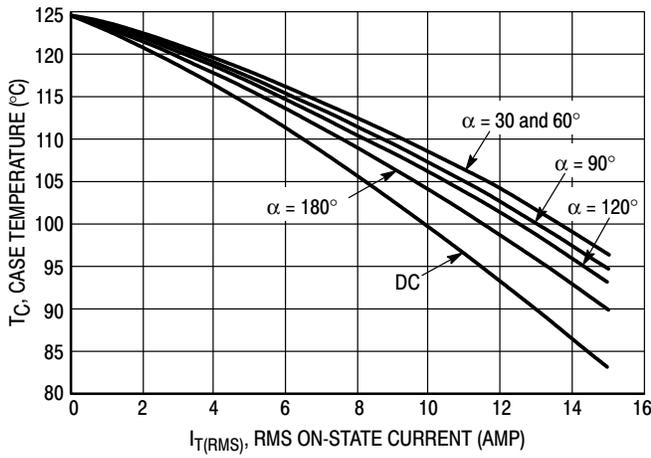
Figure 1. RMS Current Derating
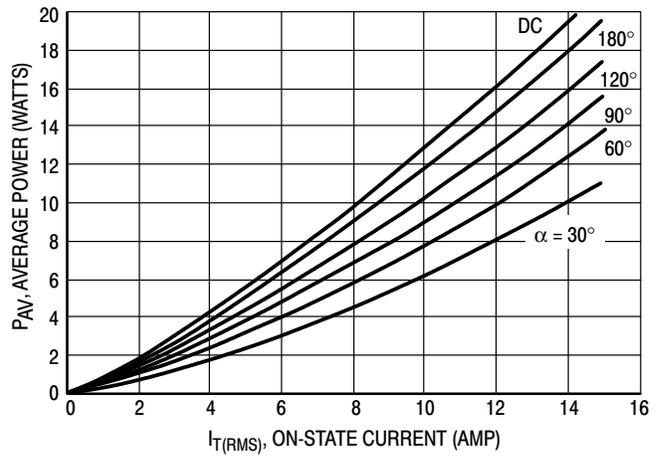
Figure 2. On−State Power Dissipation
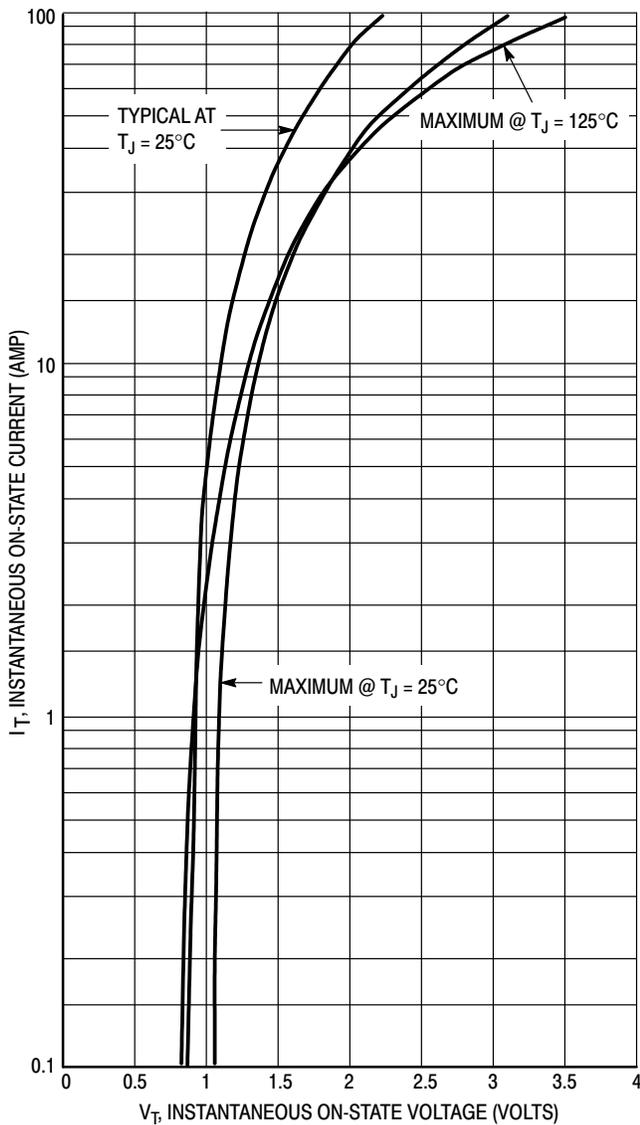
Figure 3. On−State Characteristics
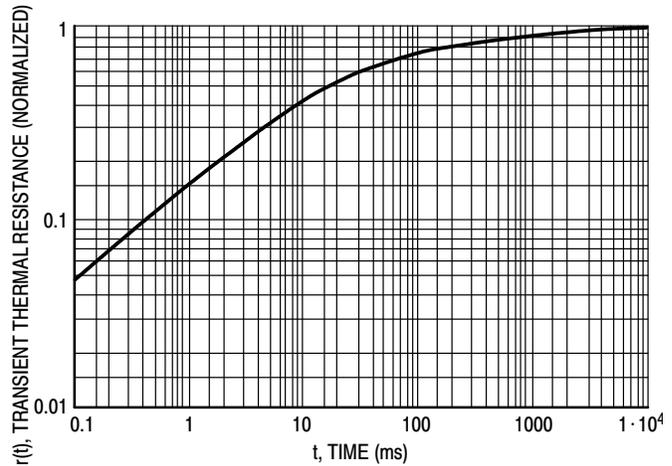
Figure 4. Transient Thermal Response
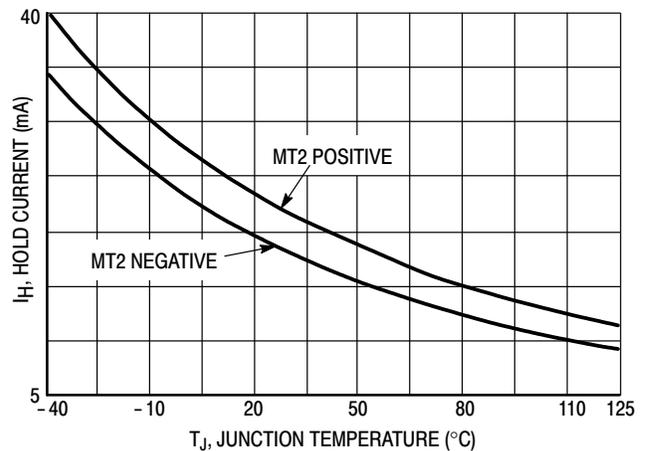
Figure 5. Hold Current Variation
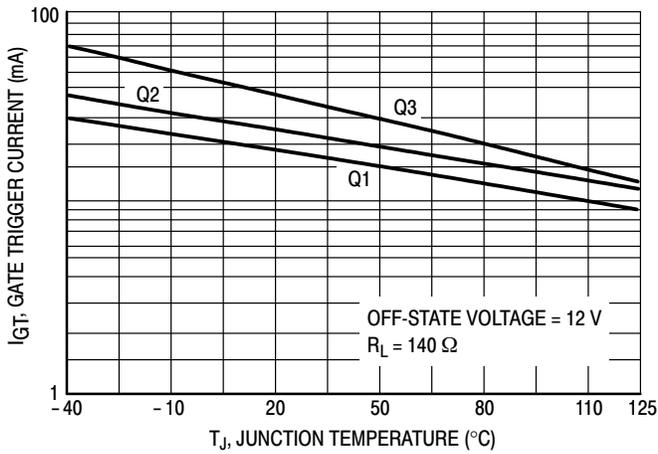
Figure 6. Typical Holding Current versus Junction Temperature
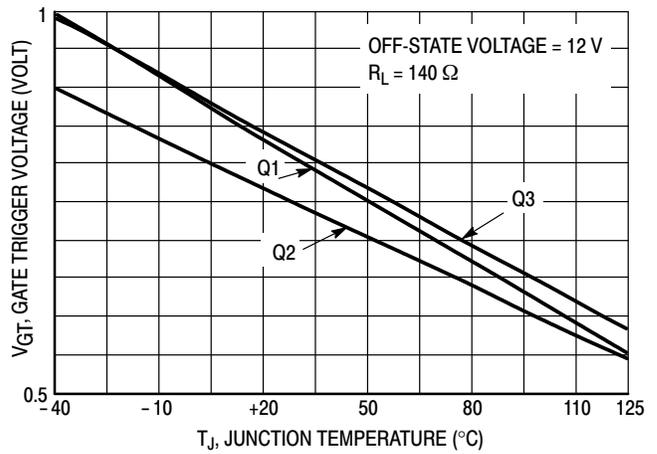
Figure 7. Gate Trigger Voltage versus Junction Temperature
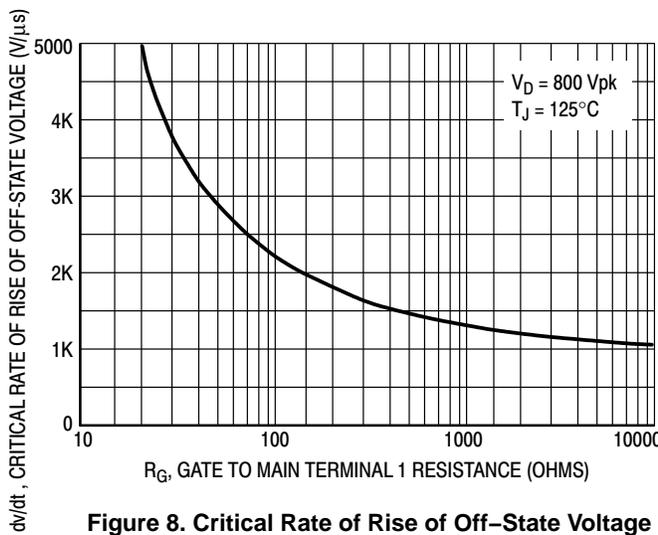
Figure 8. Critical Rate of Rise of Off−State Voltage (Exponential)
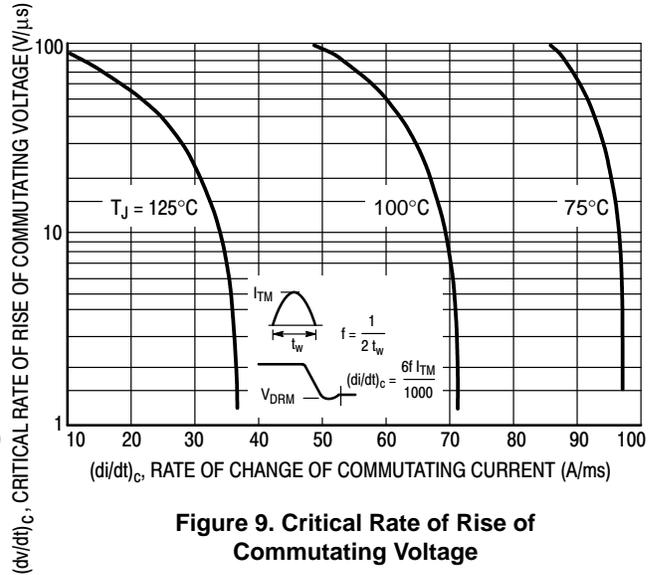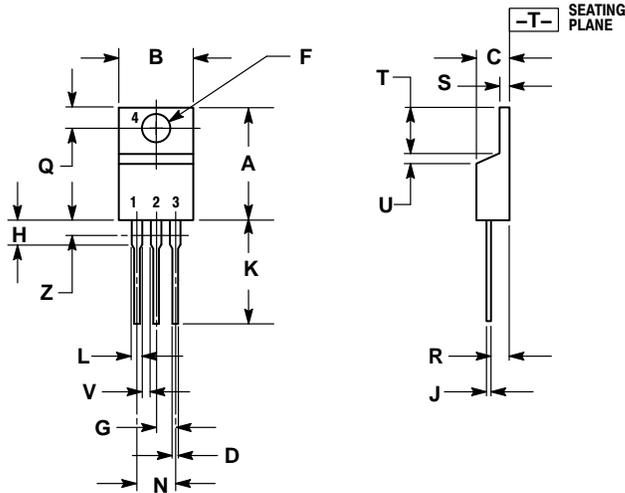
Figure 9. Critical Rate of Rise of Commutating Voltage
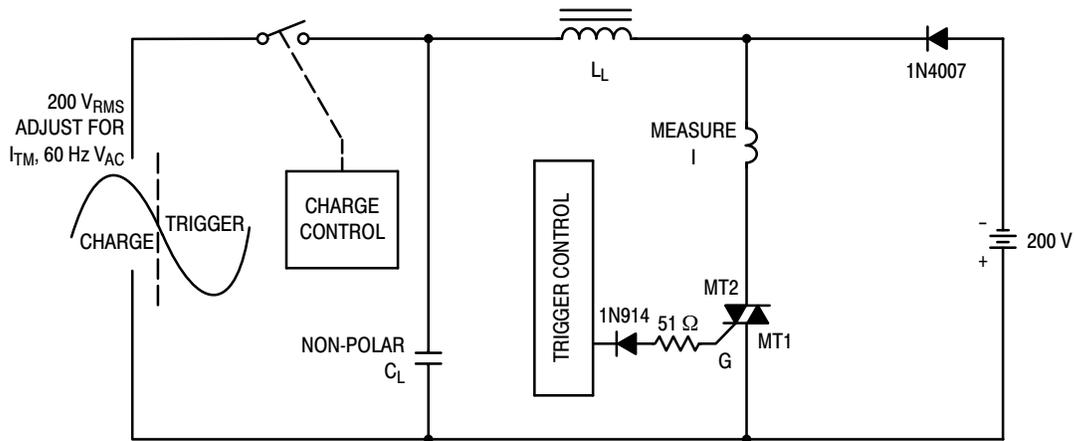
Note: Component values are for verification of rated (di/dt)$_C$. See AN1048 for additional information.

Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)$_c$

PACKAGE DIMENSIONS

TO–220
CASE 221A–09
ISSUE AH

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

PUBLICATION ORDERING INFORMATION